

Part Number

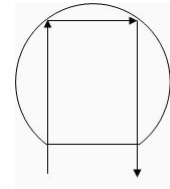
Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	380.00 +/- 3.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00 μ m	Guaranteed by Process
	7.0	Bow	<40.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<40.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	380.00 +/- 3.00 μ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.003 - 0.007 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with lasermarking	Wafer Vendor
DeviceSilicon	18.0	LPD Count	<30.00pcs	@0.3 μ m, Tencor 6220 particle counter
	19.0	Scratches	0	Bright Light, 100% (note 2)
	20.0	Haze	none	Bright Light, 100% (note 2)

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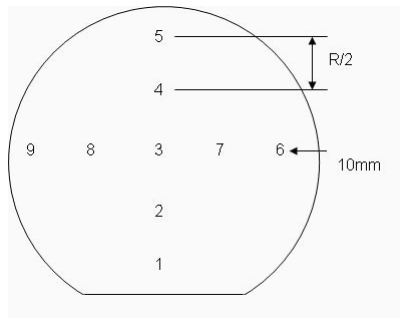
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information